



BT150S-600R

SCR

17 March 2014

Product data sheet

1. General description

Planar passivated SCR with sensitive gate in a SOT428 (DPAK) surface mountable plastic package. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Direct triggering from low power drivers and logic ICs
- Surface mountable package

3. Applications

- General purpose switching
- Protection Circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage	[1]	-	-	600	V
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4; Fig. 5	-	-	35	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 111\text{ }^{\circ}\text{C}$; Fig. 2; Fig. 3	-	-	4	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	15	200	μA

[1] Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

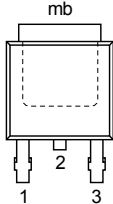



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p style="text-align: center;">DPAK (SOT428)</p>	
2	A	anode ^[1]		
3	G	gate		
mb	A	mounting base; connected to anode		

[1] It is not possible to connect to pin 2 of the SOT428 package.

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT150S-600R	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		[1]	-	600	V
V_{RRM}	repetitive peak reverse voltage			-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 111\text{ °C}$; Fig. 1		-	2.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 111\text{ °C}$; Fig. 2 ; Fig. 3		-	4	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5		-	35	A
		half sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$		-	38	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN		-	6.1	A^2s
di_T/dt	rate of rise of on-state current	$I_T = 10\text{ A}$; $I_G = 50\text{ mA}$; $dI_G/dt = 50\text{ mA}/\mu s$		-	50	$A/\mu s$
I_{GM}	peak gate current			-	2	A
V_{RGM}	peak reverse gate voltage			-	5	V
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	$^{\circ}C$
T_j	junction temperature		[2]	-	125	$^{\circ}C$

[1] Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

[2] Operation above 110 $^{\circ}C$ may require the use of a gate to cathode resistor of 1k Ω or less.

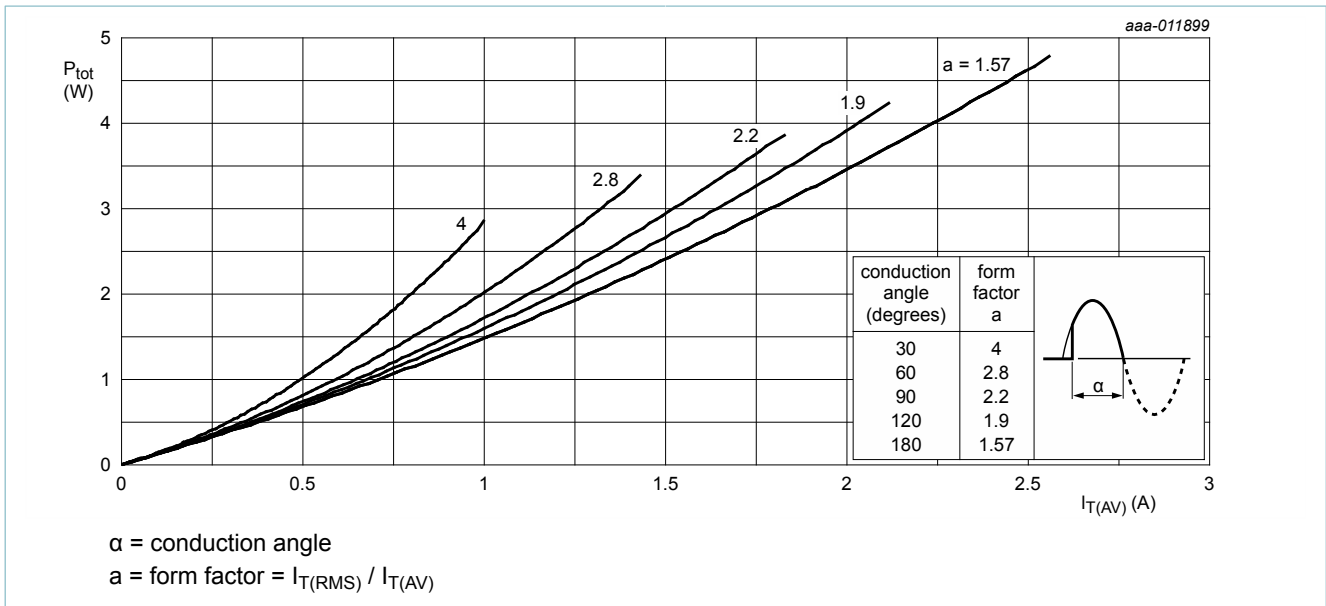


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

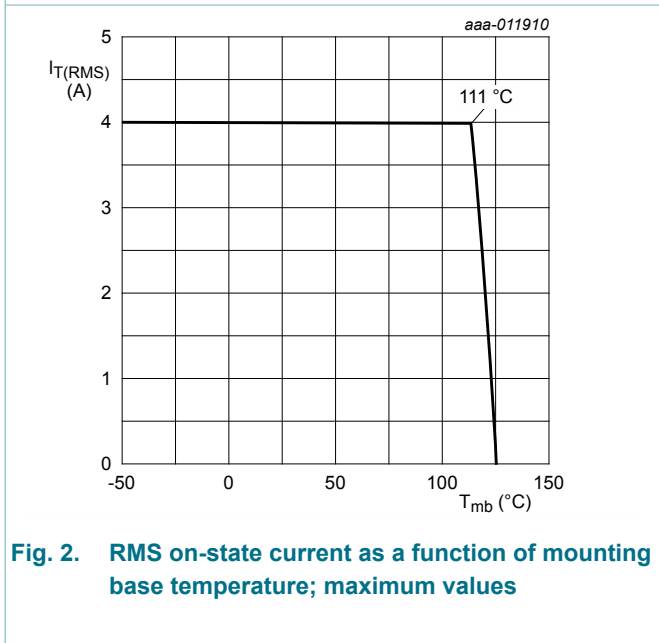


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

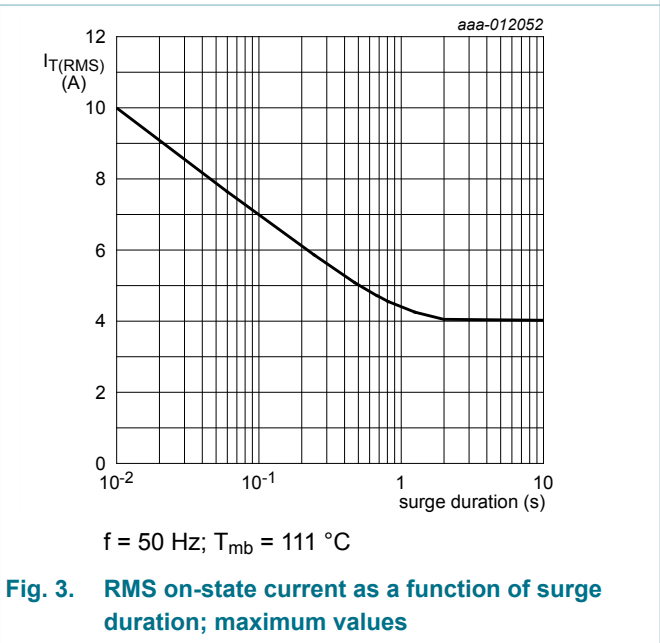


Fig. 3. RMS on-state current as a function of surge duration; maximum values

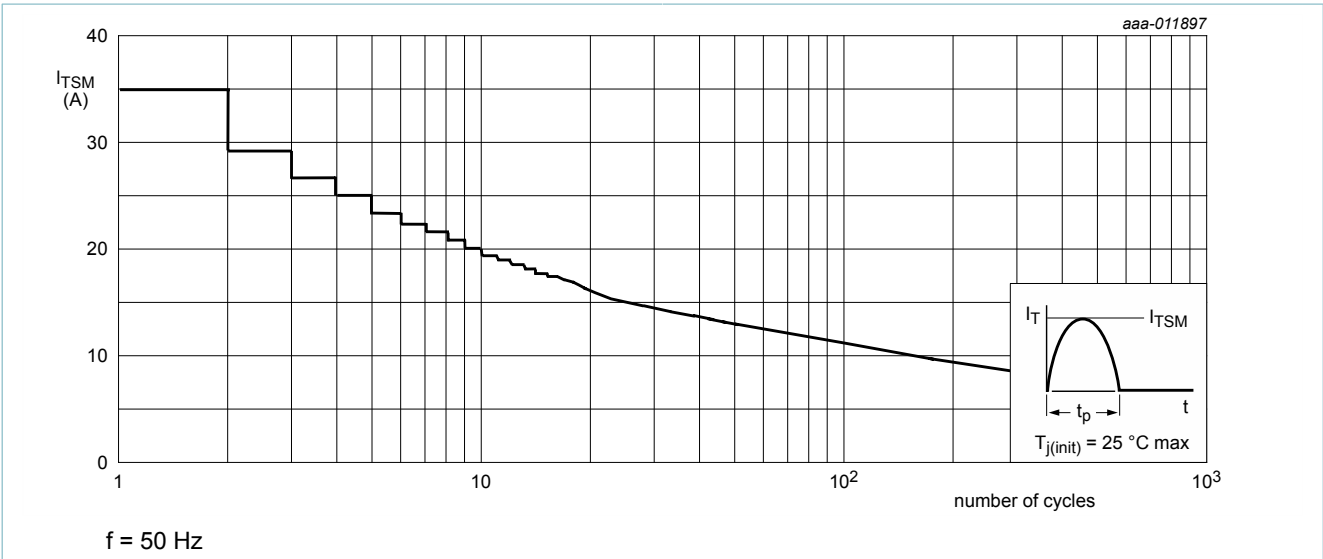


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

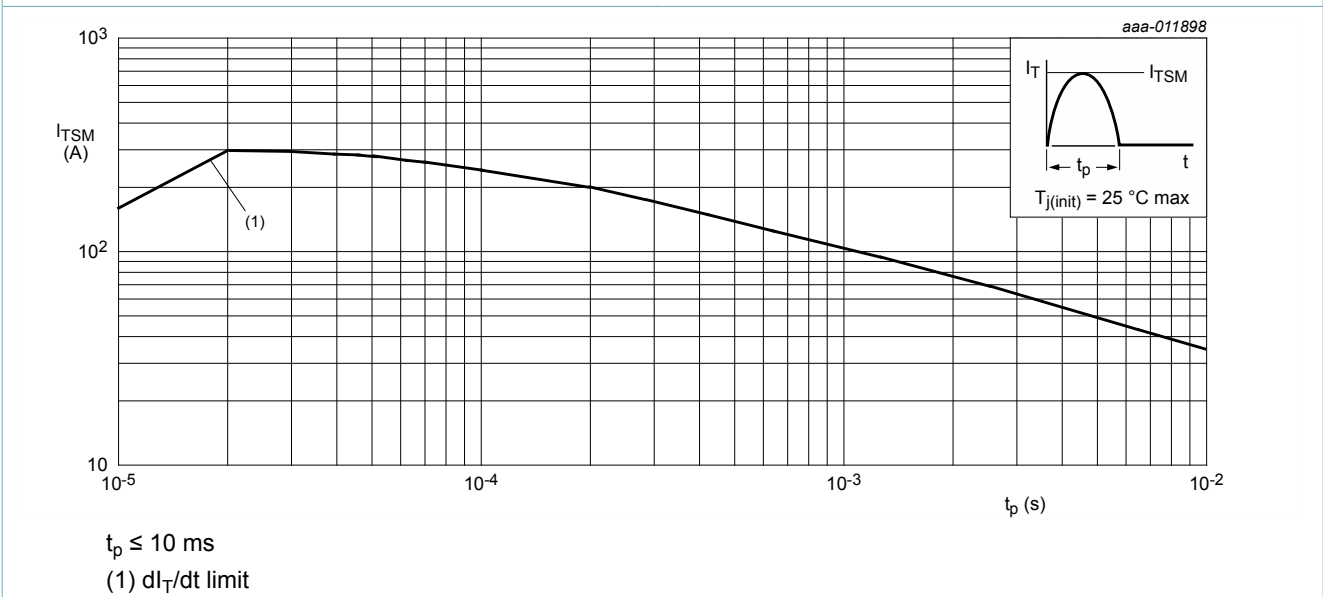
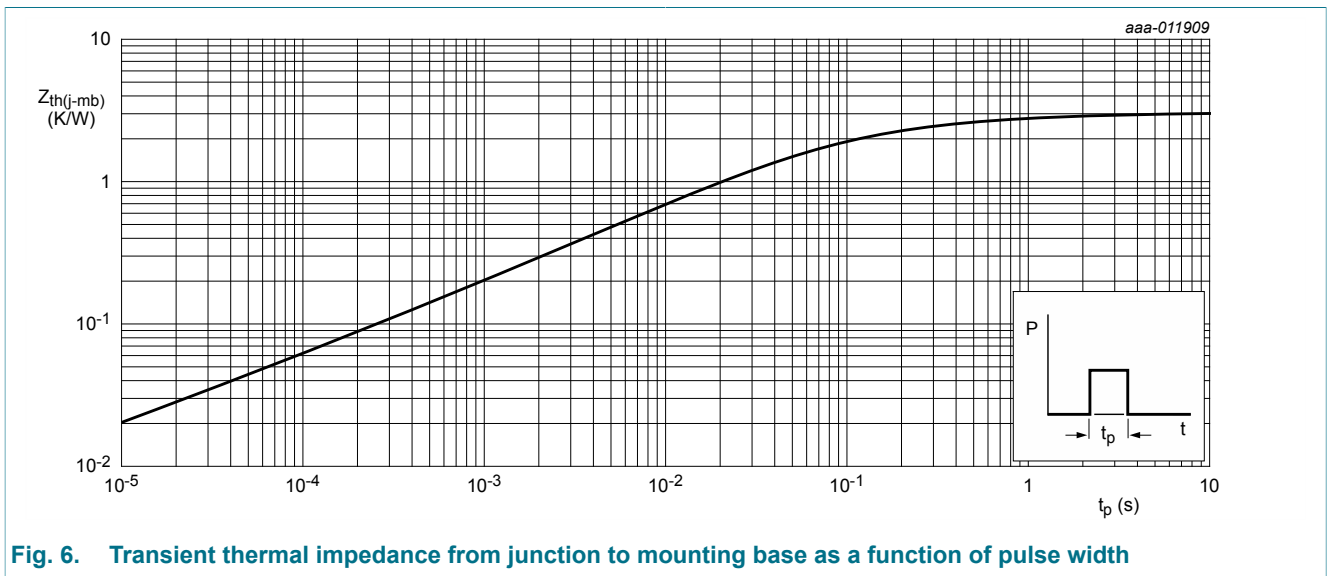


Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint	-	75	-	K/W



9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7	-	15	200	μA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 8	-	0.17	10	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	0.1	6	mA
V_T	on-state voltage	$I_T = 5\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.23	1.8	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11	-	0.4	1	V
		$V_D = 600\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 110\text{ °C}$; Fig. 11	0.1	0.2	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
I_R	reverse current	$V_R = 600\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 100\ \Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 12	-	50	-	$\text{V}/\mu\text{s}$
t_{gt}	gate-controlled turn-on time	$I_{TM} = 10\text{ A}$; $V_D = 600\text{ V}$; $I_G = 5\text{ mA}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$	-	2	-	μs
t_q	commutated turn-off time	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ °C}$; $I_{TM} = 8\text{ A}$; $V_R = 10\text{ V}$; $(dI_T/dt)_M = 10\text{ A}/\mu\text{s}$; $dV_D/dt = 2\text{ V}/\mu\text{s}$; $R_{GK} = 1\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM})	-	100	-	μs

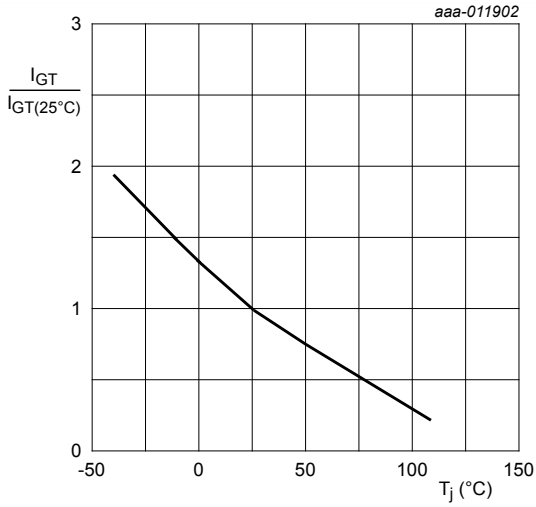


Fig. 7. Normalized gate trigger current as a function of junction temperature

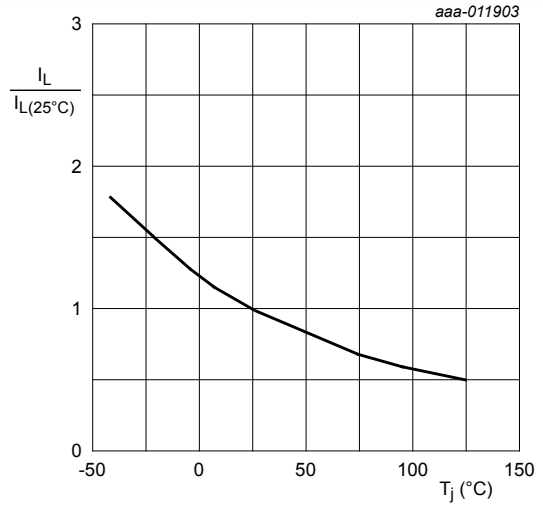


Fig. 8. Normalized latching current as a function of junction temperature
 $R_{GK} = 1 \text{ k}\Omega$

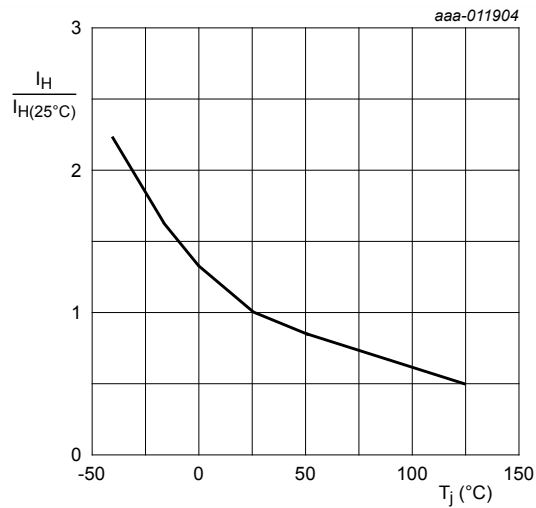


Fig. 9. Normalized holding current as a function of junction temperature
 $R_{GK} = 1 \text{ k}\Omega$

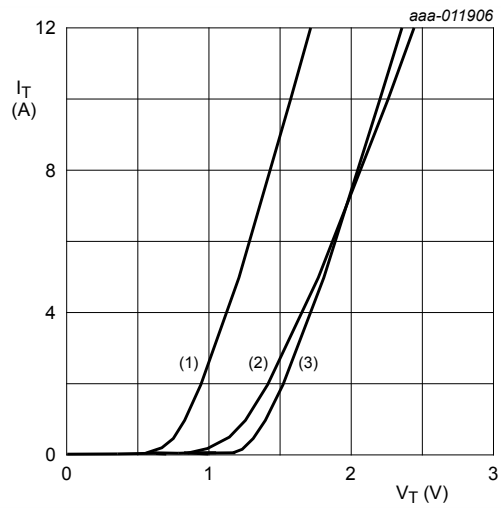
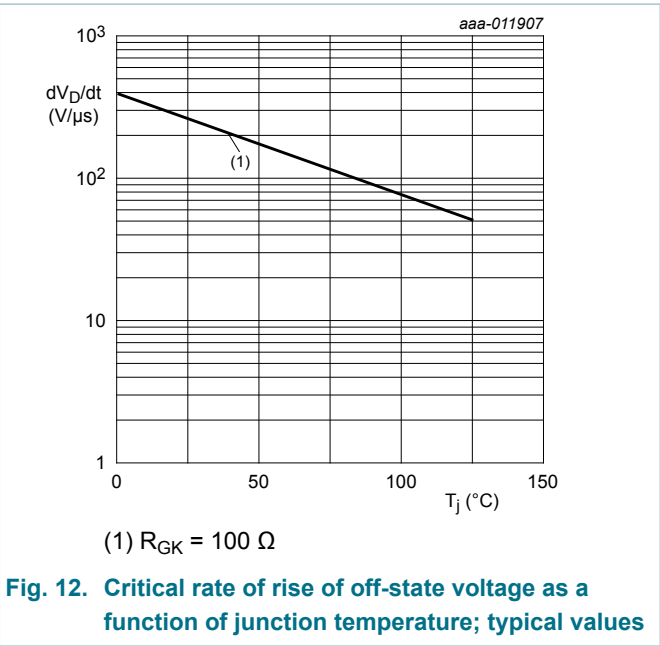
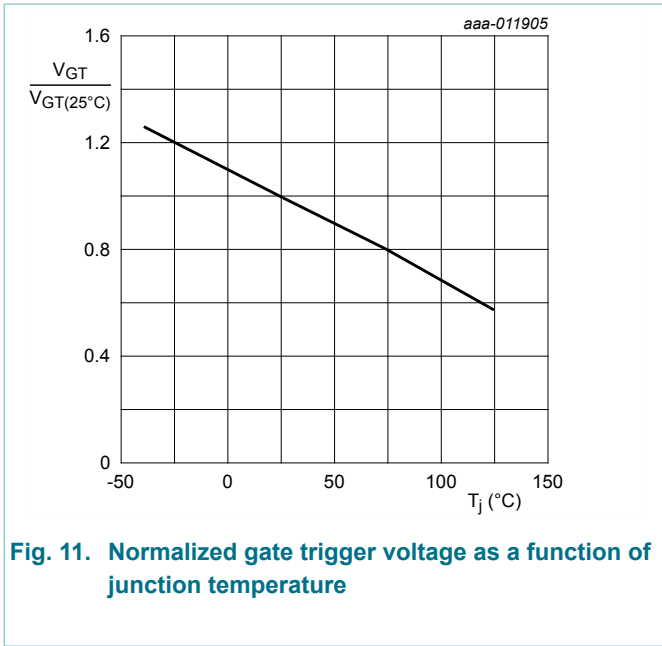
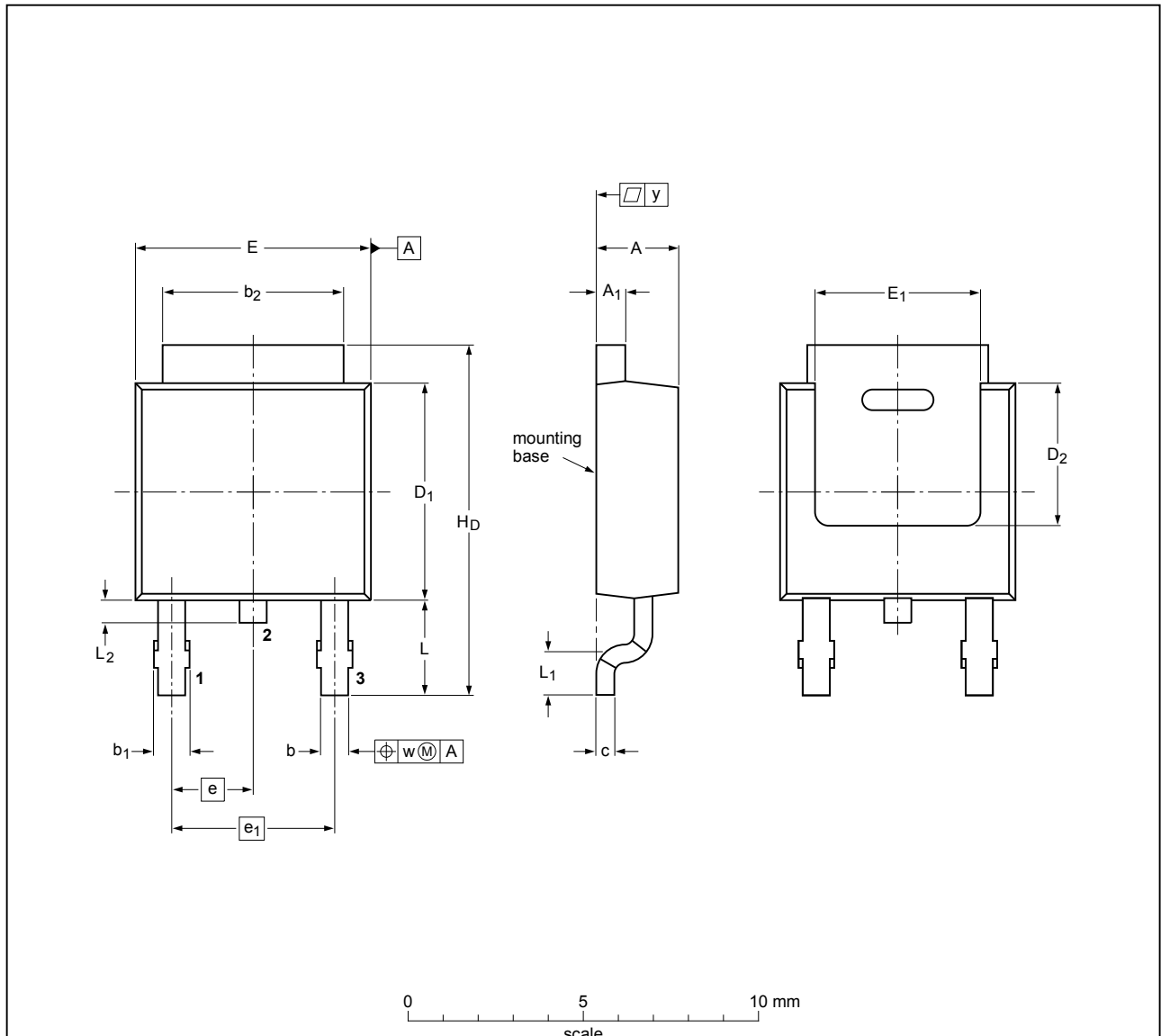


Fig. 10. On-state current as a function of on-state voltage
 $V_o = 1.26 \text{ V}; R_s = 0.099 \Omega$
 (1) $T_j = 125^\circ\text{C}$; typical values
 (2) $T_j = 125^\circ\text{C}$; maximum values
 (3) $T_j = 25^\circ\text{C}$; maximum values



10. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) SOT428



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	b ₂	c	D ₁	D ₂ min	E	E ₁ min	e	e ₁	H _D	L	L ₁ min	L ₂	w	y max
mm	2.38 2.22	0.93 0.46	0.89 0.71	1.1 0.9	5.46 5.00	0.56 0.20	6.22 5.98	4.0	6.73 6.47	4.45	2.285	4.57	10.4 9.6	2.95 2.55	0.5	0.9 0.5	0.2	0.2

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT428		TO-252	SC-63		06-02-14 06-03-16

Fig. 13. Package outline DPAK (SOT428)

11. Soldering

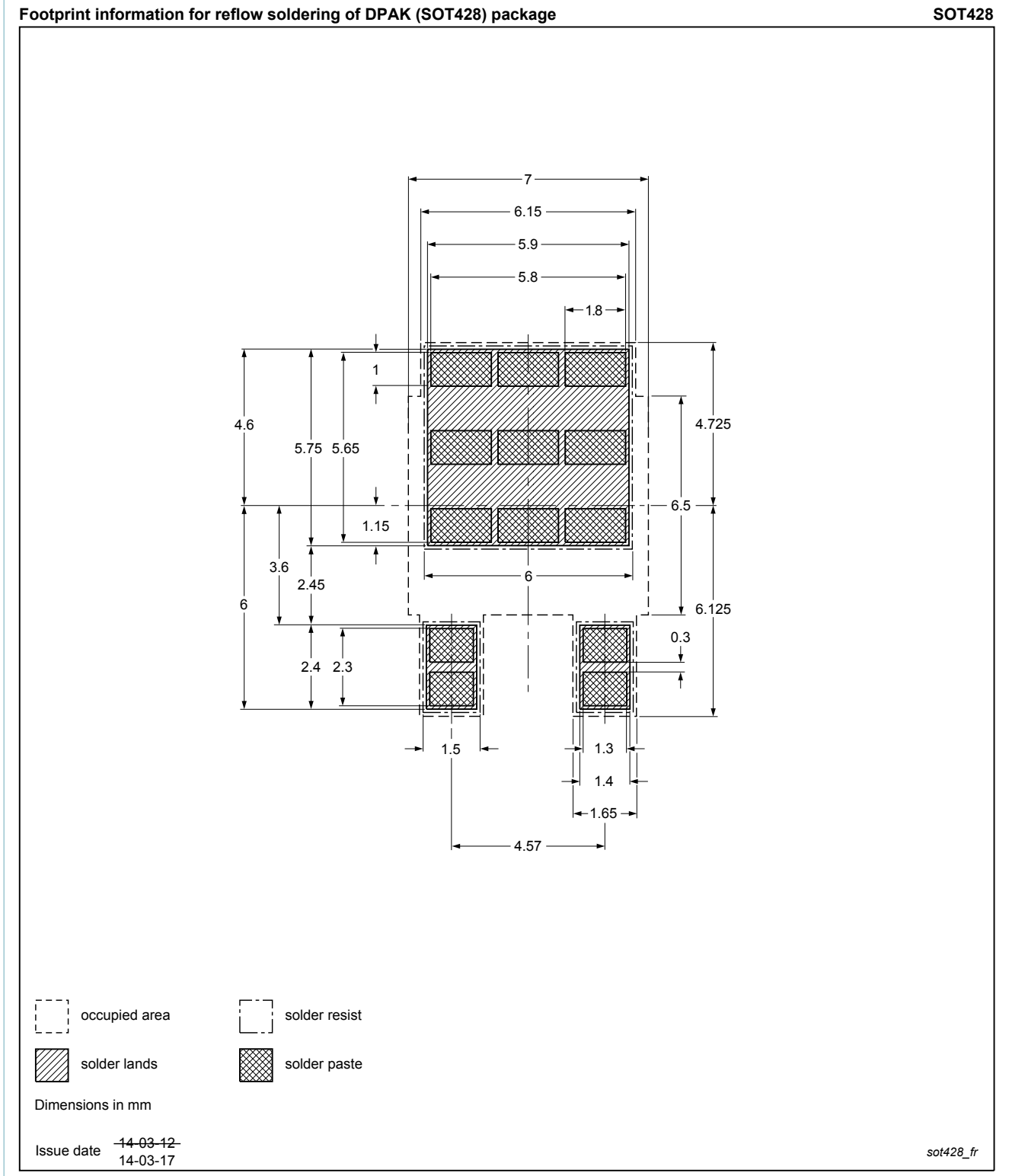


Fig. 14. Reflow soldering footprint for DPAK (SOT428)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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